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 Name of Examination : **Winter 2020** - (Preview)

 Course Code & Course Name : **IN201U - Analog Electronics**

 Generated At : **19-04-2022 10:36:28**

 Maximum Marks : **60**

 Duration : **3 Hrs**
[Edit](#) [Print](#) [View Answer Key](#) [Close](#) **Answer Key Submission Type:** Marking scheme with model answers and solutions of numerical

Instructions:

1. All questions are compulsory.
2. Illustrate your answer with suitable figures/sketches wherever necessary.
3. Assume suitable additional data; if required.
4. Use of logarithmic table, drawing instruments and non programmable calculators is allowed.
5. Figures to the right indicate full marks.

1) Solve any three sub-questions.

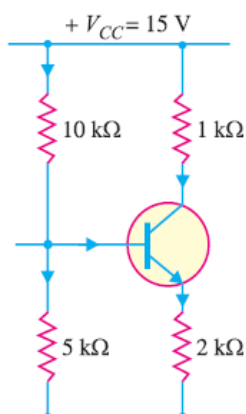
- a) Discuss the behaviour of p-n junction diode under forward and reverse biased conditions. [5]
- b) What is Clamper Circuit? Classify and explain Clampers. [5]
- c) Calculate the reverse saturation current of a diode if the current at 0.2V forward bias is 0.1mA at a temperature of 25°C and the ideality factor is 1.5. [5]
- d) Compare CE, CC and CB configurations. [5]

2) Solve any three sub-questions.

- a) Draw the circuit diagram of a voltage divider bias and derive expression for Stability factor. [5]
- b) Draw the circuit diagram of a push-pull amplifier. Explain its operation. Discuss advantages and disadvantages. [5]
- c) Explain working of Class A amplifier. state its applications. [5]
- d) Explain the Input and output characteristics of transistor in Common Base Configuration. [5]

3) Solve any three sub-questions.

- a) Describe the construction and working principle of Enhancement mode and depletion mode MOSFET and draw its characteristics. [5]
- b) Figure shows the voltage divider bias method. Draw the d.c. load line and determine the operating point. Assume the transistor to be of silicon [5]



- c) Draw the small signal model of FET. Compare it with model of BJT. [5]
 - d) State advantages of Negative feedback in amplifiers. [5]
- 4) a) Discuss biasing of Enhancement MOSFET. Derive equation for Drain current. [5]**
- b) Write note on [10]**
- i. Hartley Oscillator.
 - ii. Photodiode.

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